

	Type	L #	Hits	Search Text	Time Stamp
1	BRS	L1	36	(RTA or (rapid adj3 thermal adj3 anneal\$3)) same before same after same electrode	2002/10/30 17:37

US-PAT-NO: 5953619

DOCUMENT-IDENTIFIER: US 5953619 A

TITLE: Semiconductor device with perovskite capacitor and  
its manufacture  
method

----- KWIC -----

After the PZT dielectric film 28 is deposited and before or  
after the upper  
electrode layer 29 is deposited, an annealing process in an  
O.sub.2 atmosphere  
is performed. For example, the annealing process is  
performed for about 5  
seconds at 850.degree. C. in an O.sub.2 atmosphere at one  
atm. Such an  
annealing process can be performed by using a rapid thermal  
anneal (RTA)  
system. Instead of RTA, an annealing process may be  
performed by using a  
resistance heating furnace at 800.degree. C. or higher for  
10 minutes or  
longer, for example, at 800.degree. C. for 30 minutes.